SNx4LVC00A クワッド、2 入力、正論理 NAND ゲート

1 特長

- JESD 22 を上回る ESD 保護
  - 2000V 人体モデル
  - 1000V 荷電デバイス モデル
- SN74LVC00A 動作範囲 1.65V ~ 3.6V
- SN54LVC00A 動作範囲 2V ~ 3.6V
- SNx4LVC00A –40°C ~ +85°C および –40°C ~ +125°C で動作を規定
- SN54LVC00A -55°C ~ +125°Cで動作を規定
- 5.5V までの入力電圧に対応
- 最大 t_{pd} 4.3ns (3.3V 時)
- V_{OLP} 標準値 (出力グランド バウンス) < 0.8V (V_{CC} = 3.3V、T_A = 25°C)
- V_{OHV} 標準値 (出力 V_{OH} アンダーシュート) > 2V (V_{CC} = 3.3V、T_A = 25°C)
- JESD 17 準拠
  250mA 超のラッチアップ性能
- MIL-PRF-38535 準拠の製品については、特に記述のない限り、すべてのパラメータはテスト済みです。その他のすべての製品については、量産プロセスにすべてのパラメータのテストが含まれているとは限りません。

2 アプリケーション

- AV レシーバ
- オーディオ ドック：ポータブル
- Blu-ray プレーヤおよびホーム シアター
- MP3 プレーヤ / レコーダ
- パーソナル デジタル アシスタント(PDA)
- 電源：テレコム / サーバー AC/DC 電源：シングル コントローラ：アナログおよびデジタル
- ソリッド ステート ドライブ (SSD)：クライアントおよびエンタープライズ
- テレビ：LCD、デジタル、高解像度 (HDTV)
- タブレット：エンタープライズ
- ビデオ分析：サーバー
- ワイヤレス ヘッドセット、キーボード、マウス

3 概要

SN54LVC00A クワッド 2 入力正論理 NAND ゲートは 2.7V ~ 3.6V の V_{CC} で動作するように設計されており、SN74LVC00A クワッド 2 入力正論理 NAND ゲートは 1.65V ~ 3.6V の V_{CC} で動作するように設計されて います。

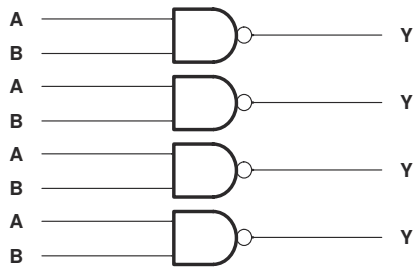
SNx4LVC00A デバイスは、ブール関数 $Y = \overline{A \cdot B}$、すなわち $Y = \overline{A} + \overline{B}$ を正論理で実行します。

入力は 3.3V または 5V のデバイスから駆動できます。この機能により、3.3V と 5V が混在するシステム環境での変換装置としてこのデバイスを使用できます。

製品情報

部品番号	パッケージ (1)	パッケージ サイズ (2)	本体サイズ (3)
SNx4LVC00A	BQA (WQFN、14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC、14)	8.65mm × 6mm	8.65 mm × 3.91 mm
	DB (SSOP、14)	6.2mm × 7.8mm	6.20 mm × 5.30 mm
	NS (SOP、14)	10.2mm × 7.8mm	10.30 mm × 5.30 mm
	PW (TSSOP、14)	5mm × 4.4mm	5.00 mm × 4.40 mm
	RGY (VQFN、14)	3.5mm × 3.5mm	3.50 mm × 3.50 mm
	FK (LCCC、20)	8.9mm × 8.9mm	8.89 mm × 8.89 mm
	J (CDIP、14)	19.55mm × 7.9mm	19.55 mm × 6.7mm
	W (CFP、14)	9.21mm × 9mm	9.21mm × 6.28mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。
(3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



概略回路図

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4 Pin Configuration and Functions

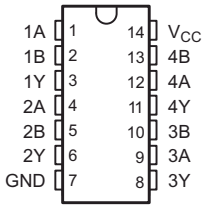
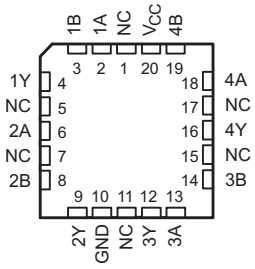


図 4-1. SN54LVC00A J or W Package; SN74LVC00A D, DB, NS, or PW Package 14-Pin CDIP, CFP SOIC, SSOP, SO, or TSSOP (Top View)



NC - No internal connection

図 4-2. SN54LVC00A FK Package 20-Pin LCCC (Top View)

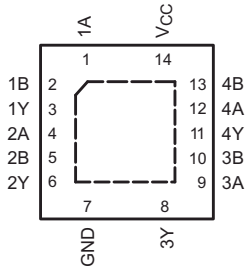


図 4-3. SN74LVC00A BQA or RGY Package 14-Pin WQFN or VQFN (Top View)

表 4-1. Pin Functions

PIN					TYPE	DESCRIPTION
NAME	SN74LVC00A		SN54LVC00A			
	D, DB, NS, PW	BQA, RGY	J, W	FK		
1A	1	1	1	2	I	Gate 1 input
1B	2	2	2	3	I	Gate 1 input
1Y	3	3	3	4	O	Gate 1 output
2A	4	4	4	6	I	Gate 2 input
2B	5	5	5	8	I	Gate 2 input
2Y	6	6	6	9	O	Gate 2 output
GND	7	7	7	10	I	Ground Pin
3Y	8	8	8	12	O	Gate 3 output
3A	9	9	9	13	I	Gate 3 input
3B	10	10	10	14	I	Gate 3 input
4Y	11	11	11	16	O	Gate 4 output
4A	12	12	12	18	I	Gate 4 input
4B	13	13	13	19	I	Gate 4 input
V_{CC}	14	14	14	20	—	Positive supply
NC	—	—	—	1	—	No Connection
				5		
				7		
				11		
				15		
				17		

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Output voltage (2) (3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
V_{CC}	Continuous current through GND			±100	mA
P_{tot}	Power dissipation(4) (5)	T_A = –40°C to +125°C		500	mW
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.
(4) For the D package: above 70°C, the value of P_{tot} derates linearly with 8 mW/K.
(5) For the DB, NS, and PW packages: above 60°C, the value of P_{tot} derates linearly with 5.5 mW/K.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions, SN54LVC00A

over operating free-air temperature range (unless otherwise noted)(1)

			SN54LVC00A –55°C to +125°C		UNIT
			MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Recommended Operating Conditions, SN74LVC00A

over operating free-air temperature range (unless otherwise noted)(1)

			SN74LVC00A						UNIT
			T_A = 25°C		–40°C to 85°C		–40°C to 125°C		
			MIN	MAX	MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V
		Data retention only	1.5		1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		0.65 × V_{CC}		0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		1.7		1.7		
		V_{CC} = 2.7 V to 3.6 V	2		2		2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}		0.35 × V_{CC}		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7		0.7		0.7	
		V_{CC} = 2.7 V to 3.6 V		0.8		0.8		0.8	
V_I	Input voltage		0	5.5	0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4		–4		–4	mA
		V_{CC} = 2.3 V		–8		–8		–8	
		V_{CC} = 2.7 V		–12		–12		–12	
		V_{CC} = 3 V		–24		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4		4		4	mA
		V_{CC} = 2.3 V		8		8		8	
		V_{CC} = 2.7 V		12		12		12	
		V_{CC} = 3 V		24		24		24	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.5 Thermal Information

THERMAL METRIC(1)		SN74LVC00A						UNIT
		BQA (WQFN)	D (SOIC)	DB (SSOP)	NS (SOP)	PW (TSSOP)	RGY (VQFN)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.3	127.8	140.4	123.8	150.8	92.1	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.6 Electrical Characteristics, SN54LVC00A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	SN54LVC00A –55°C to +125°C		UNIT
				MIN	MAX	
V_{OH}	I_{OH} = –100 µA		2.7 V to 3.6 V	V_{CC} – 0.2		V
	I_{OH} = –12 mA		2.7 V	2.2		
			3 V	2.4		
	I_{OH} = –24 mA		3 V	2.2		
V_{OL}	I_{OL} = 100 µA		2.7 V to 3.6 V		0.2	V
	I_{OL} = 12 mA		2.7 V		0.4	
	I_{OL} = 24 mA		3 V		0.55	
I_I	V_I = 5.5 V or GND		3.6 V		±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V		10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V		500	µA

5.7 Electrical Characteristics, SN74LVC00A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN74LVC00A						UNIT
			T_A = 25°C			–40°C to +85°C		–40°C to +125°C		
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	I_{OH} = –100 µA	1.65 V to 3.6 V	V_{CC} – 0.2			V_{CC} – 0.2		V_{CC} – 0.3		V
	I_{OH} = –4 mA	1.65 V	1.29			1.2		1.05		
	I_{OH} = –8 mA	2.3 V	1.9			1.7		1.55		
	I_{OH} = –12 mA	2.7 V	2.2			2.2		2.05		
		3 V	2.4			2.4		2.25		
	I_{OH} = –24 mA	3 V	2.3			2.2		2		
V_{OL}	I_{OL} = 100 µA	1.65 V to 3.6 V			0.1		0.2		0.3	V
	I_{OL} = 4 mA	1.65 V			0.24		0.45		0.6	
	I_{OL} = 8 mA	2.3 V			0.3		0.7		0.85	
	I_{OL} = 12 mA	2.7 V			0.4		0.4		0.6	
	I_{OL} = 24 mA	3 V			0.55		0.55		0.8	
I_I	V_I = 5.5 V or GND	3.6 V			±1		±5		±20	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			1		10		40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500		500		5000	µA
C_i	V_I = V_{CC} or GND	3.3 V		5						pF

5.8 Switching Characteristics, SN54LVC00A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN54LVC00A –55°C to +125°C		UNIT
				MIN	MAX	
t_{pd}	A or B	Y	2.7 V		5.1	ns
			3.3 V ± 0.3 V	1	4.3	

5.9 Switching Characteristics, SN74LVC00A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN74LVC00A							UNIT
				T_A = 25°C			–40°C to +85°C		–40°C to +125°C		
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1.8 V ± 0.15 V	1	6	12	1	12.5	1	14	ns
			2.5 V ± 0.2 V	1	4.6	5.9	1	6.4	1	7.9	
			2.7 V	1	4.3	4.9	1	5.1	1	6.5	
			3.3 V ± 0.3 V	1	3.5	4.1	1	4.3	1	5.5	
$t_{sk(o)}$			3.3 V ± 0.3 V					1		1.5	ns

5.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	f = 10 MHz	1.8 V	18	pF
			2.5 V	18	
			3.3 V	19	

5.11 Typical Characteristics

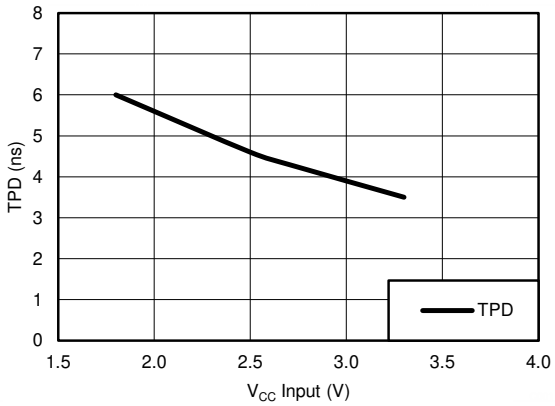
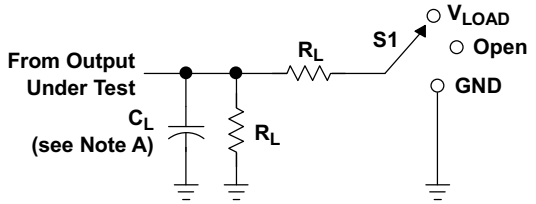


図 5-1. TPD vs V_{CC} (T_A = 25°C)

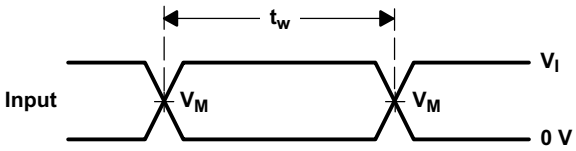
6 Parameter Measurement Information



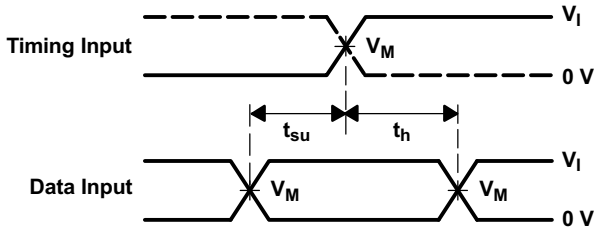
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

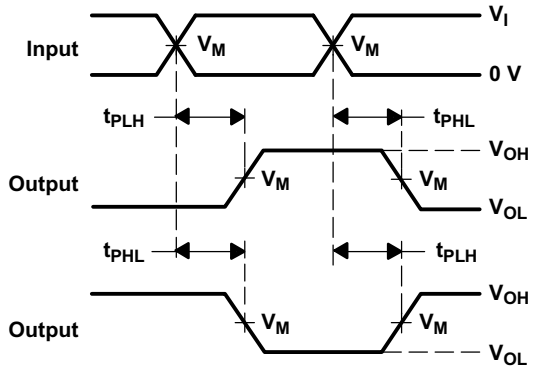
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



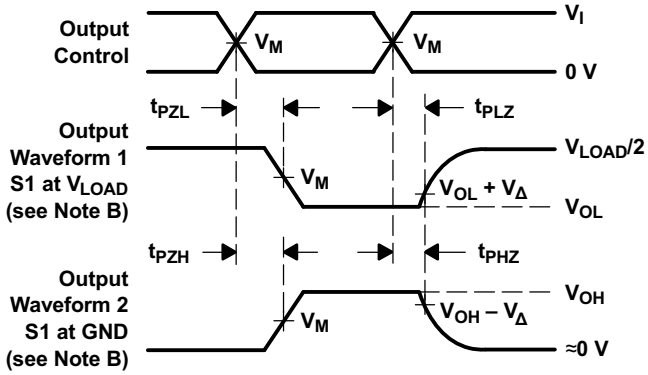
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

図 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The maximum sink and source current is 24 mA.

Inputs can be driven from 1.8-V, 2.5-V, 3.3-V (LVTTL), or 5-V (CMOS) devices. This feature allows the use of this device as translators in a mixed-system environment.

7.2 Functional Block Diagram

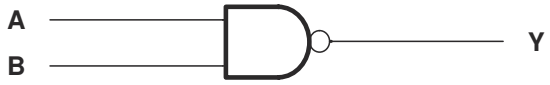


図 7-1. Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

7.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *セクション 5.1* must be followed at all times.

7.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modelled as a resistor in parallel with the input capacitance given in the *セクション 5.6* and *セクション 5.7*. The worst case resistance is calculated with the maximum input voltage, given in the *セクション 5.1*, and the maximum input leakage current, given in the *セクション 5.6* and *セクション 5.7*, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by Δt/Δv in *セクション 5.3* and *セクション 5.4* to avoid excessive currents and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

7.3.3 Clamp Diodes

The inputs and outputs to this device have negative clamping diodes.

> **注意**
>
> Voltages beyond the values specified in the *セクション 5.1* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

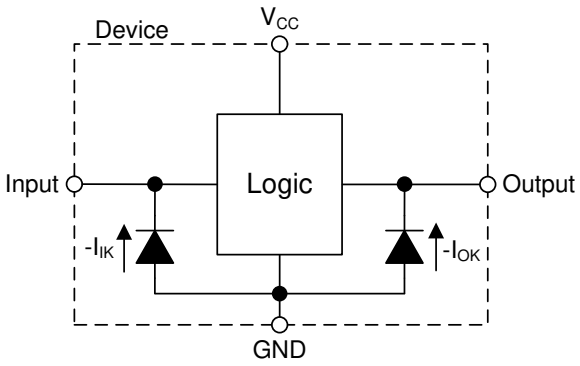


図 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.4 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *セクション 5.1*.

7.4 Device Functional Modes

表 7-1 lists the functional modes of SN54LVC00A and SN74LVC00A.

表 7-1. Function Table (Each Gate)

INPUTS		OUTPUT Y
A	B	
H	H	L
L	X	H
X	L	H

8 Application and Implementation

注

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8.1 Application Information

SN74LVC00A is a high-drive CMOS device that can be used for a multitude of buffer-type functions. It can produce 24 mA of drive current at 3.3 V. Therefore, this device is ideal for driving multiple inputs and for high-speed applications up to 100 MHz. The inputs and outputs are 5.5-V tolerant allowing the device to allowing the device to perform mixed-voltage input down translation. For example the A input can be 3.3 V and the B input can be 5 V, while V_{CC} = 2.5 V and the device will operate properly to output a 2.5 V signal.

8.2 Typical Application

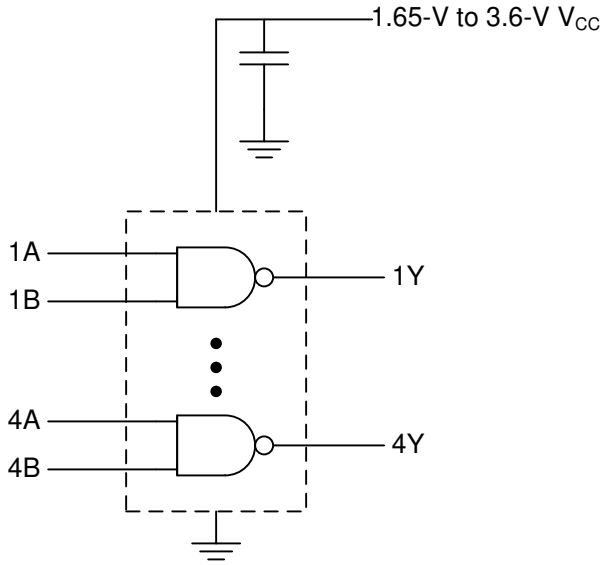

図 8-1. Typical NAND Gate Application and Supply Voltage

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads; therefore, routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

1. Recommended Input Conditions
   - Rise time and fall time specs: See (Δt/ΔV) in the *セクション 5.4* table.
   - Specified high and low levels: See (V_{IH} and V_{IL}) in the *セクション 5.4* table.
   - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
2. Recommended Output Conditions
   - Load currents should not exceed 25 mA per output and 50 mA total for the part.
   - Outputs should not be pulled above 5.5 V.

8.2.3 Application Curve

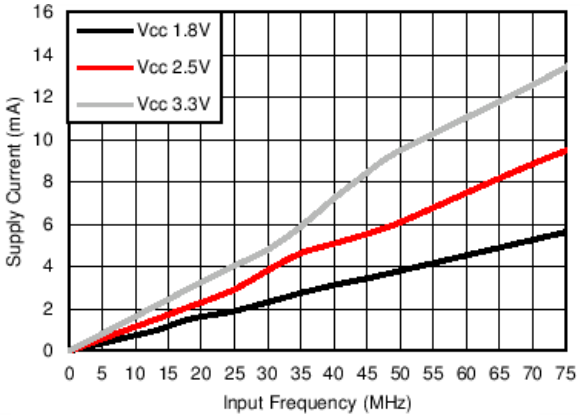

図 8-2. I_{CC} vs Frequency

Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *セクション 5.4* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µF is recommended; if there are multiple V_{CC} pins, then 0.01 µF or 0.022 µF is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 µF and a 1 µF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple bit logic devices inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. セクション 8.3.2 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver.

8.3.2 Layout Example

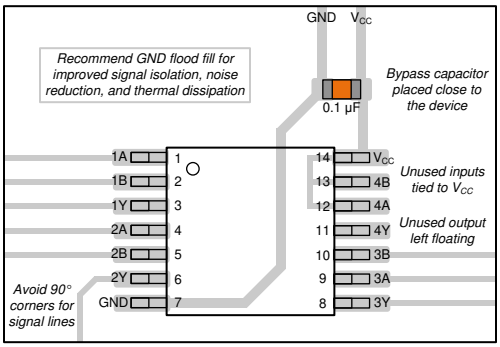

図 8-3. Layout Diagram for the SNx4LVC00A

9 Device and Documentation Support

9.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

表 9-1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54LVC00A	Click here	Click here	Click here	Click here	Click here
SN74LVC00A	Click here	Click here	Click here	Click here	Click here

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 サポート・リソース

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9.3.1 Community Resources

9.4 Trademarks

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9.6 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

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資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision T (May 2024) to Revision U (July 2024)	Page
• Updated RθJA values: D = 86 to 127.8, all values in °C/W	5
• Added *Typical Characteristics*	7

Changes from Revision S (March 2024) to Revision T (May 2024)	Page
• Updated RθJA values: DB = 96 to 140.4, NS = 76 to 123.8, PW = 113 to 150.8, RGY = 47 to 92.1; Updated DB, NS, PW, and RGY packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W	5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9753301Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301Q2A SNJ54LVC 00AFK	Samples
5962-9753301QCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QC A SNJ54LVC00AJ	Samples
5962-9753301QDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QD A SNJ54LVC00AW	Samples
5962-9753301VDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301VD A SNV54LVC00AW	Samples
SN74LVC00ABQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00AD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ADBRG4	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ADE4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ANSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ANSRG4	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00APW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWE4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWG4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC00APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWRE4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ARGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC00A	Samples
SNJ54LVC00AFK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301Q2A SNJ54LVC 00AFK	Samples
SNJ54LVC00AJ	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QC A SNJ54LVC00AJ	Samples
SNJ54LVC00AW	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QD A SNJ54LVC00AW	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF SN54LVC00A, SN54LVC00A-SP, SN74LVC00A :

- Catalog : SN74LVC00A, SN54LVC00A
- Automotive : SN74LVC00A-Q1, SN74LVC00A-Q1
- Enhanced Product : SN74LVC00A-EP, SN74LVC00A-EP
- Military : SN54LVC00A
- Space : SN54LVC00A-SP

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications
- Military - QML certified for Military and Defense Applications
- Space - Radiation tolerant, ceramic packaging and qualified for use in Space-based application

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